

SANYO Semiconductors DATA SHEET

P-Channel Silicon MOSFET

5LP01S — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 2.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-50	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-0.07	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-0.28	Α
Allowable Power Dissipation	PD		0.15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Llmit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-50			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-50V, VGS=0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-100μA	-0.4		-1.4	V
Forward Transfer Admittance	yfs	V _D S=-10V, I _D =-40mA	70	100		mS
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=-40mA, VGS=-4V		18	23	Ω
	R _{DS} (on)2	ID=-20mA, VGS=-2.5V		20	28	Ω
	RDS(on)3	ID=-5mA, VGS=-1.5V		30	60	Ω
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		7.4		pF
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		4.2		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-10V, f=1MHz		1.3		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		20		ns
Rise Time	t _r	See specified Test Circuit.		35		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		160		ns
Fall Time	tf	See specified Test Circuit.		150		ns

Marking: XB Continued on next page.

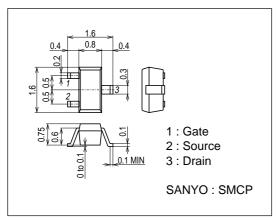
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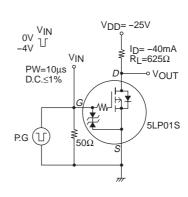
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-10V, I _D =-70mA		1.40		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-10V, I _D =-70mA		0.16		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-10V, I _D =-70mA		0.23		nC
Diode Forward Voltage	VsD	IS=-70mA, VGS=0V		-0.85	-1.2	V

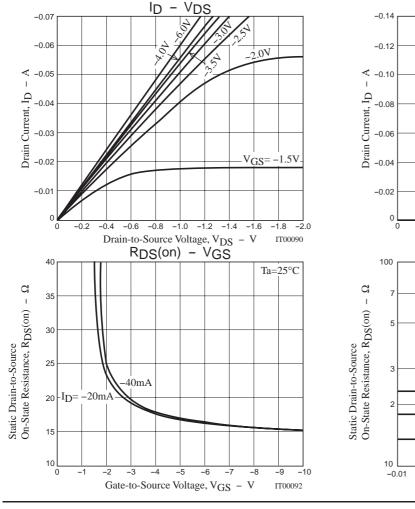
Package Dimensions

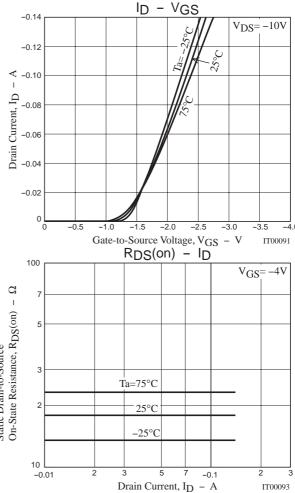
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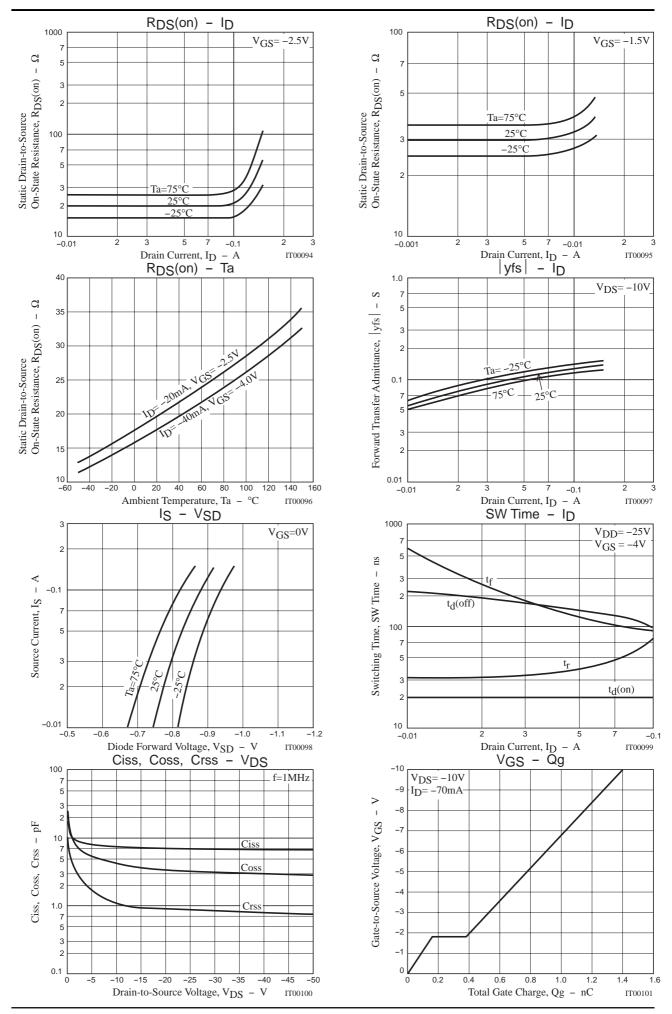


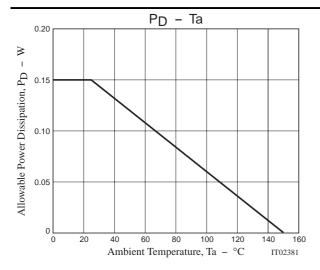
Switching Time Test Circuit











Note on usage: Since the 5LP01S is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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